

# BD253C Transistors

## Si NPN Power BJT

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Military/High-Rel N

V(BR)CEO (V) 400

V(BR)CBO (V) 900

I(C) Max. (A) 4.0

Absolute Max. Power Diss. (W) 50

Maximum Operating Temp (°C) 175°

I(CBO) Max. (A) 2.0m

@V(CBO) (V) (Test Condition)

V(CE)sat Max. (V)

@I(C) (A) (Test Condition)

@I(B) (A) (Test Condition)

h(FE) Min. Current gain. 5.0

h(FE) Max. Current gain. 10<sup>Å</sup>

@I(C) (A) (Test Condition) 3.0

@V(CE) (V) (Test Condition) 4.0

f(T) Min. (Hz) Transition Freq 25M

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

t(d) Max. (s) Delay time. 1.5u<sup>®</sup>

t(r) Max. (s) Rise time 1.0u